

Silicon Photo Diodes

Model No. SD-06BF

Optoelectronic device

◆ Features

- Sensitive to the visible light only: $\lambda_p=560\text{nm}$
- Suitable for EE cameras, exposure meters, and others
- High reliability



◆ Absolute Maximum Ratings

Ta = 25°C

Parameter	Symbol	Value	Unit
DC Reverse Voltage	V _R	20	V
Operating Temperature	Topr	-20 ~ +60	°C
Storage Temperature	Tstg	-25 ~ +80	°C

◆ Electro-optical Characteristics

Ta = 25°C

Parameter	Symbol	MIN	TYP	MAX	Unit	Condition
Sensitive Range	λ	350		730	nm	Equivalent energy
Peak sensitive wavelength	λ_p		560		nm	Equivalent energy
Short Circuit Current	I _{sc}	0.1			μA	100Lx
Dark current	I _d			5	pA	V _R =1V. RH≤65%
Shortcircuit current temp. coefficient	β_T		--		%/°C	100Lx
Dark current temp. coefficient	α_T		--		Times/10°C	V _R =1V. RH≤65%
Terminal capacitance	C _T		160		pF	V _R =0V, f=1MHz
Spectral sensitivity	ΔIR		--	--	%	$\lambda=700\text{nm}$, I _{sc} ratio

Package	Ceramic
Active area	1.27mm ²